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## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



## 1. General description

Planar passivated high commutation three quadrant triac in a SOT1292 (IITO3P) package intended for use in circuits where high static and dynamic  $dV/dt$  and high  $dI/dt$  can occur. This "series BT" triac will commute the full RMS current at the maximum rated junction temperature ( $T_{j(max)} = 150\text{ °C}$ ) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

## 2. Features and benefits

- High current TRIAC
- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by  $dV/dt$
- High junction operating temperature capability ( $T_{j(max)} = 150\text{ °C}$ )
- High voltage capability
- Least sensitive gate for highest noise immunity
- Low thermal resistance
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Insulated tab rated at 2500 V rms

## 3. Applications

- Applications subject to high temperature ( $T_{j(max)} = 150\text{ °C}$ )
- High current / high surge applications
- High power / industrial controls - e.g. heating, motors, lighting

## 4. Quick reference data

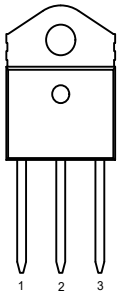
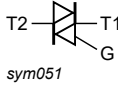
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 110\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	40	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	400	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	-	440	A
$T_j$	junction temperature		-	-	150	°C
<b>Static characteristics</b>						

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; Fig. 7	-	-	50	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; Fig. 7	-	-	50	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; Fig. 7	-	-	50	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; Fig. 9	-	-	80	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 56.6 A; T <sub>j</sub> = 25 °C; Fig. 10	-	-	1.5	V
<b>Dynamic characteristics</b>						
dV <sub>D</sub> /dt	rate of rise of off-state voltage	V <sub>DM</sub> = 536 V; T <sub>j</sub> = 150 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	1000	-	-	V/μs
dI <sub>com</sub> /dt	rate of change of commutating current	V <sub>D</sub> = 400 V; T <sub>j</sub> = 150 °C; I <sub>T(RMS)</sub> = 20 A; dV <sub>com</sub> /dt = 20 V/μs; (snubberless condition); gate open circuit	15	-	-	A/ms

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p>IITO3P (SOT1292)</p>	 <p>sym051</p>
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA440Z-800BT	IITO3P	plastic single-ended through-hole package; isolated heatsink mounted; 1 mounting hole; 3-lead TO3P	SOT1292

## 7. Marking

Table 4. Marking codes

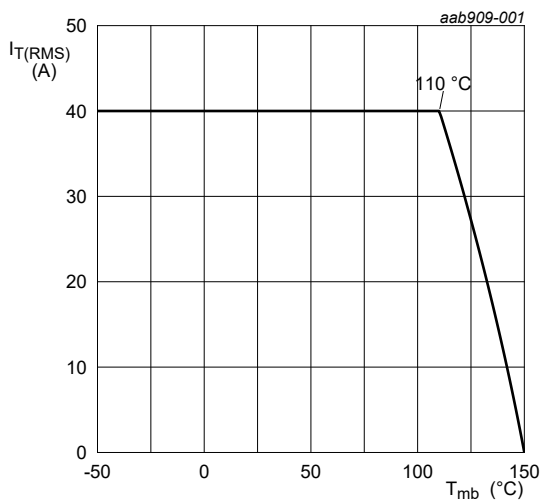
Type number	Marking code
BTA440Z-800BT	BTA440Z-800BT

## 8. Limiting values

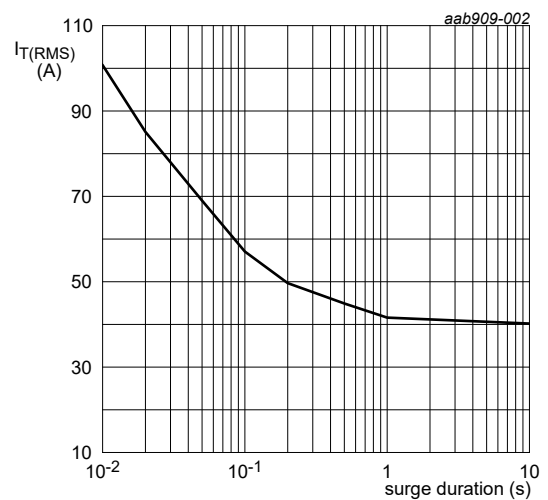
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 110\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	40	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	400	A
		full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	440	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; sine-wave pulse	-	800	A <sup>2</sup> s
$di_T/dt$	rate of rise of on-state current	$I_G = 0.2\text{ A}$	-	150	A/ $\mu$ s
$I_{GM}$	peak gate current	$t_p = 20\text{ }\mu$ s	-	8	A
$P_{GM}$	peak gate power	$t_p = 20\text{ }\mu$ s	-	40	W
$P_{G(AV)}$	average gate power		-	1	W
$T_{stg}$	storage temperature		-40	150	°C
$T_j$	junction temperature		-	150	°C

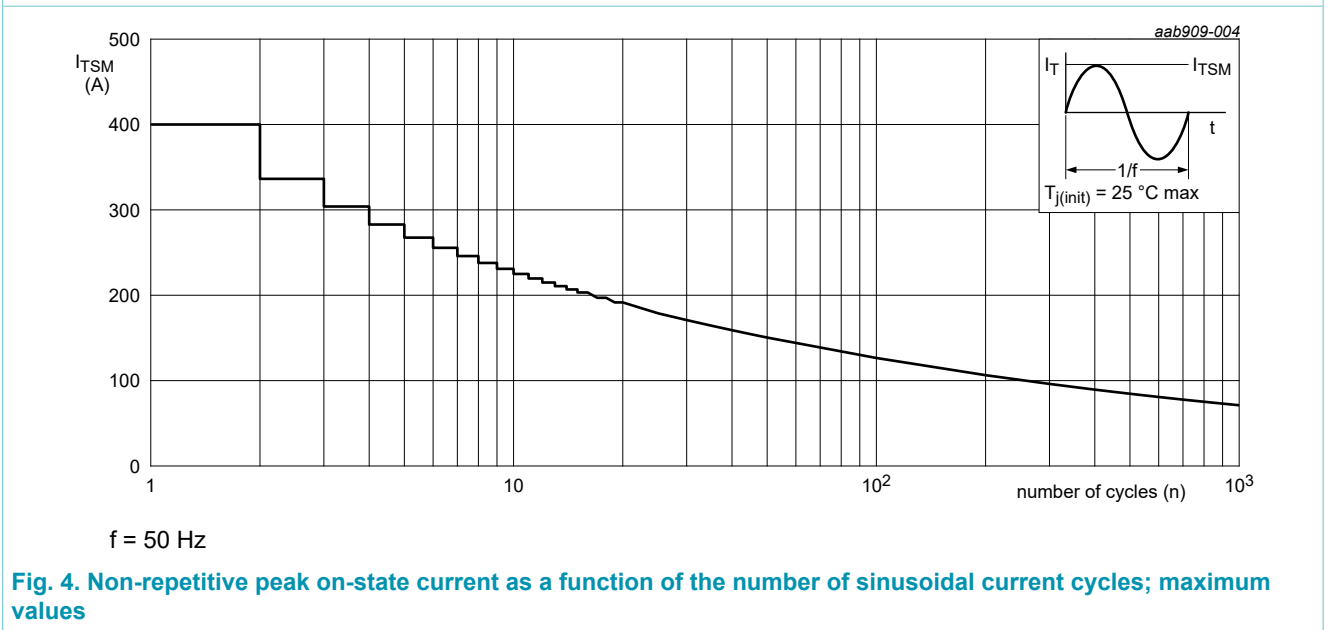
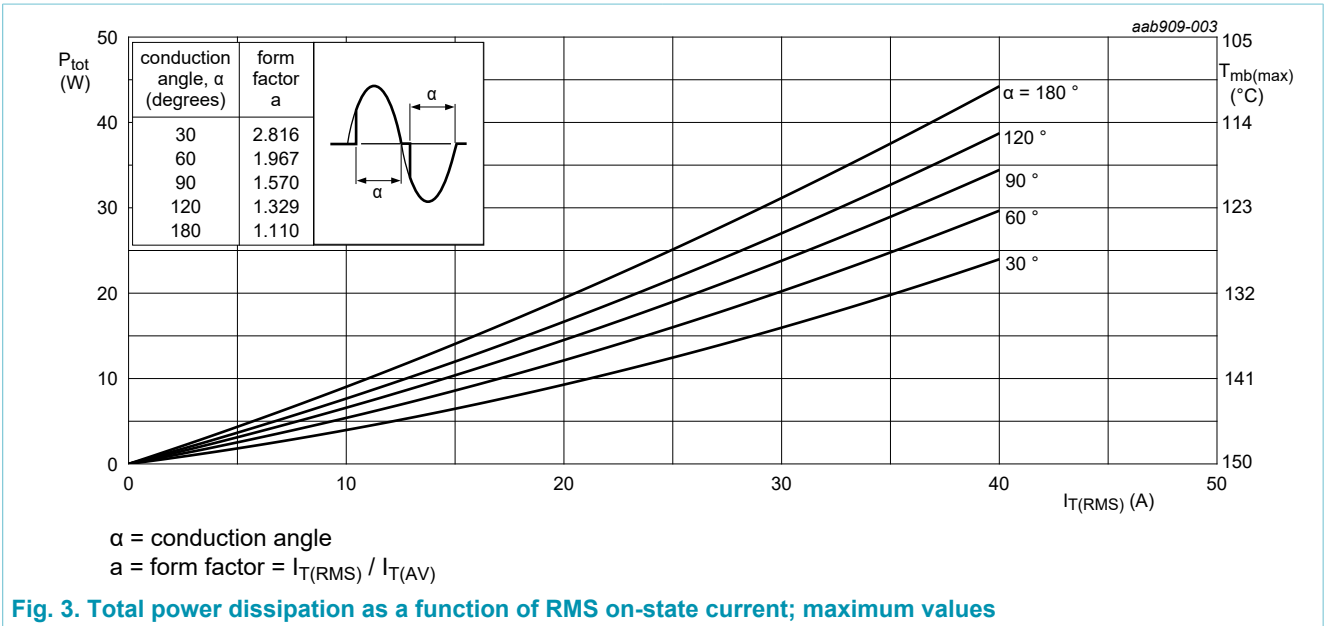


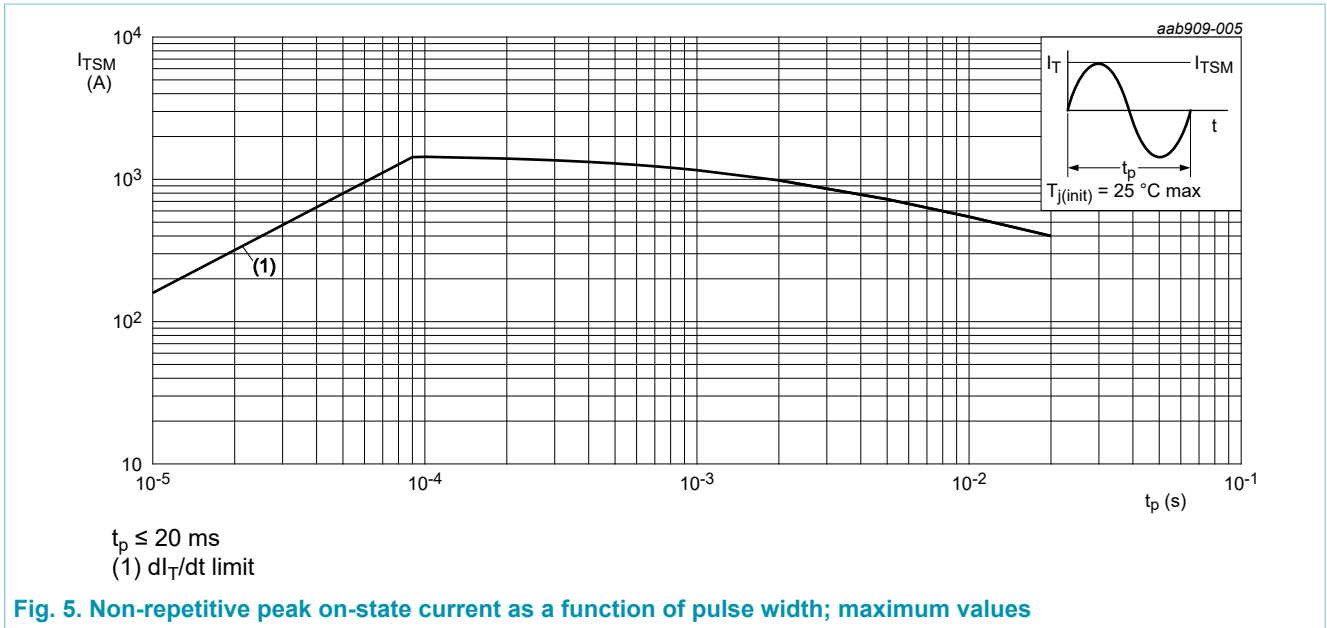
**Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values**



$f = 50\text{ Hz}$ ;  $T_{mb} = 110\text{ °C}$

**Fig. 2. RMS on-state current as a function of surge duration; maximum values**





## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<a href="#">Fig. 6</a>	-	-	0.9	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	50	-	K/W

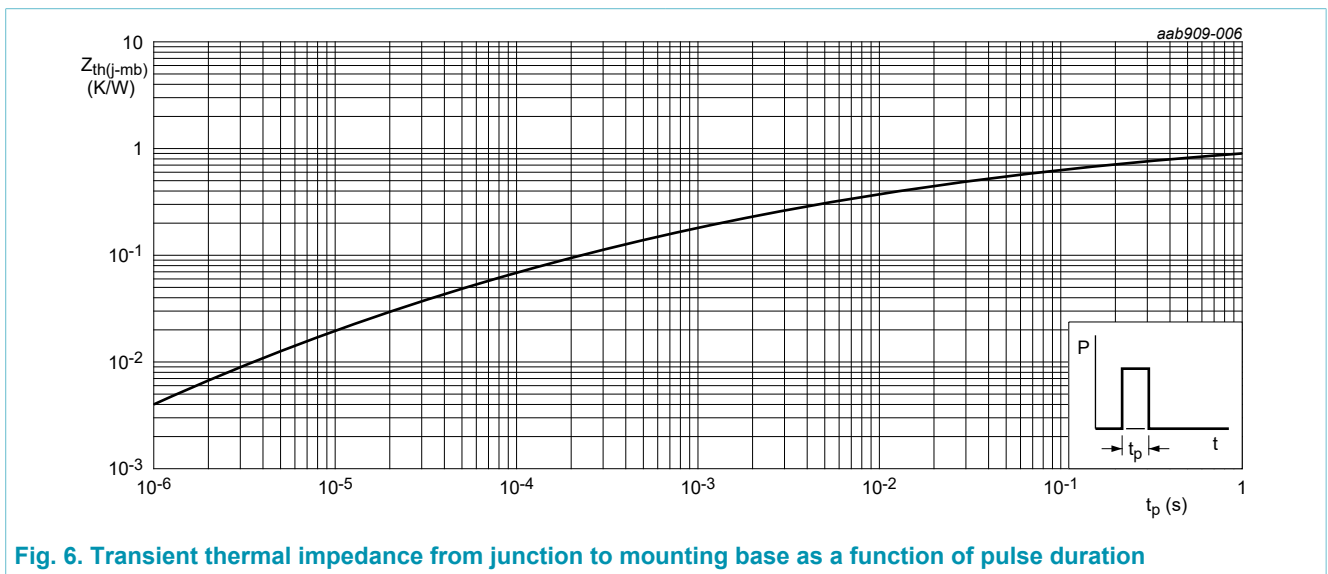


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Isolation characteristics

Table 7. Isolation characteristics

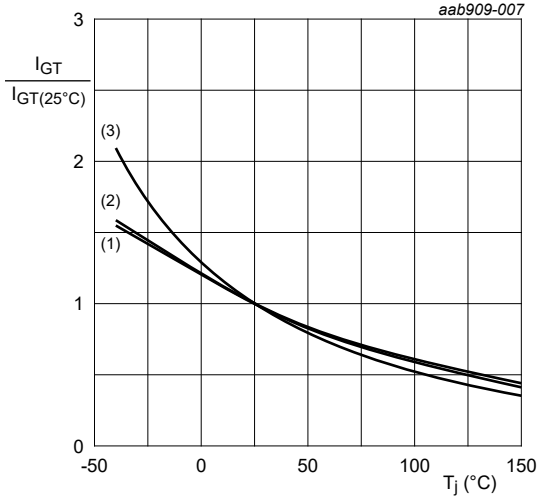
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; $50\text{ Hz} \leq f \leq 60\text{ Hz}$ ; $RH \leq 65\%$ ; $T_{mb} = 25\text{ }^\circ\text{C}$	-	-	2500	V

## 11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2+ G+;$ $T_j = 25\text{ °C};$ <a href="#">Fig. 7</a>	-	-	50	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2+ G-;$ $T_j = 25\text{ °C};$ <a href="#">Fig. 7</a>	-	-	50	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2- G-;$ $T_j = 25\text{ °C};$ <a href="#">Fig. 7</a>	-	-	50	mA
$I_L$	latching current	$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T2+ G+;$ $T_j = 25\text{ °C};$ <a href="#">Fig. 8</a>	-	-	70	mA
		$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T2+ G-;$ $T_j = 25\text{ °C};$ <a href="#">Fig. 8</a>	-	-	160	mA
		$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T2- G-;$ $T_j = 25\text{ °C};$ <a href="#">Fig. 8</a>	-	-	70	mA
$I_H$	holding current	$V_D = 12\text{ V}; T_j = 25\text{ °C};$ <a href="#">Fig. 9</a>	-	-	80	mA
$V_T$	on-state voltage	$I_T = 56.6\text{ A}; T_j = 25\text{ °C};$ <a href="#">Fig. 10</a>	-	-	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}; T_j = 25\text{ °C};$ <a href="#">Fig. 11</a>	-	0.8	1.3	V
		$V_D = 400\text{ V}; T_j = 150\text{ °C};$ <a href="#">Fig. 11</a>	0.2	0.45	-	V
$I_D$	off-state current	$V_D = 800\text{ V}; T_j = 25\text{ °C}$	-	-	10	$\mu\text{A}$
		$V_D = 800\text{ V}; T_j = 150\text{ °C}$	-	-	2	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}; T_j = 150\text{ °C}; (V_{DM} = 67\%$ of $V_{DRM});$ exponential waveform; gate open circuit	1000	-	-	$\text{V}/\mu\text{s}$
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}; T_j = 150\text{ °C}; I_{T(RMS)} = 20\text{ A};$ $dV_{com}/dt = 20\text{ V}/\mu\text{s};$ (snubberless condition); gate open circuit	15	-	-	A/ms





- (1) T2+ G+
- (2) T2+ G-
- (3) T2- G-

Fig. 7. Normalized gate trigger current as a function of junction temperature

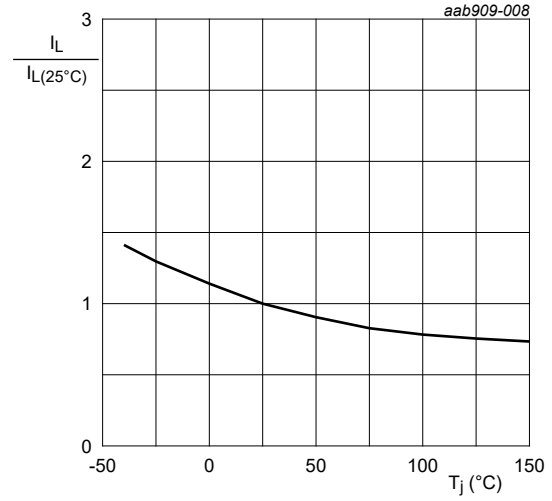


Fig. 8. Normalized latching current as a function of junction temperature

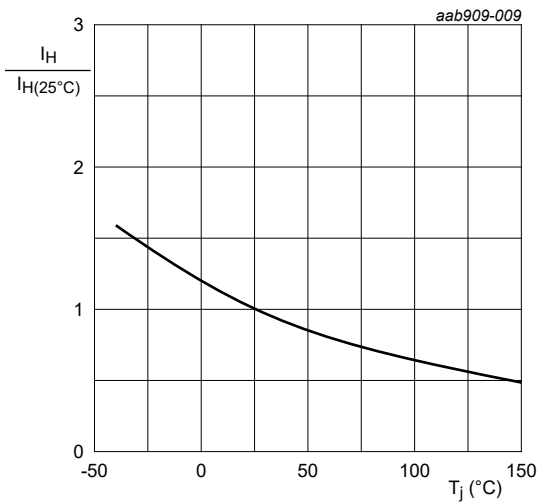
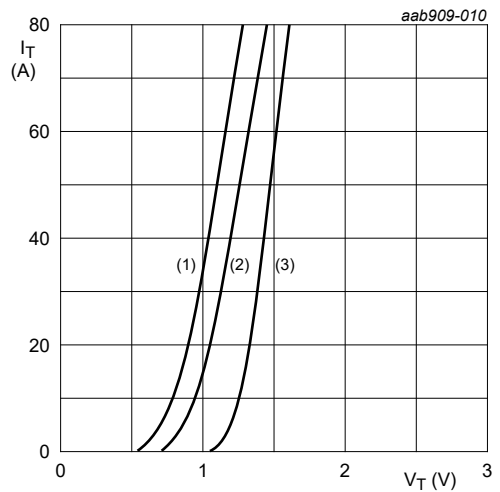


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 0.928 \text{ V}$ ;  $R_s = 0.0068 \Omega$

- (1)  $T_j = 150^\circ\text{C}$ ; typical values
- (2)  $T_j = 150^\circ\text{C}$ ; maximum values
- (3)  $T_j = 25^\circ\text{C}$ ; maximum values

Fig. 10. On-state current as a function of on-state voltage

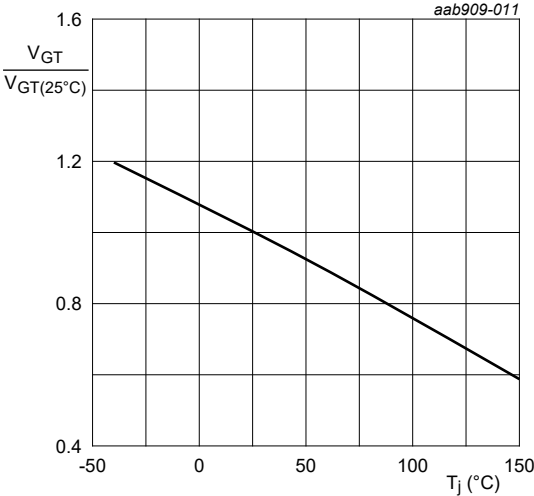


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

## 12. Package outline

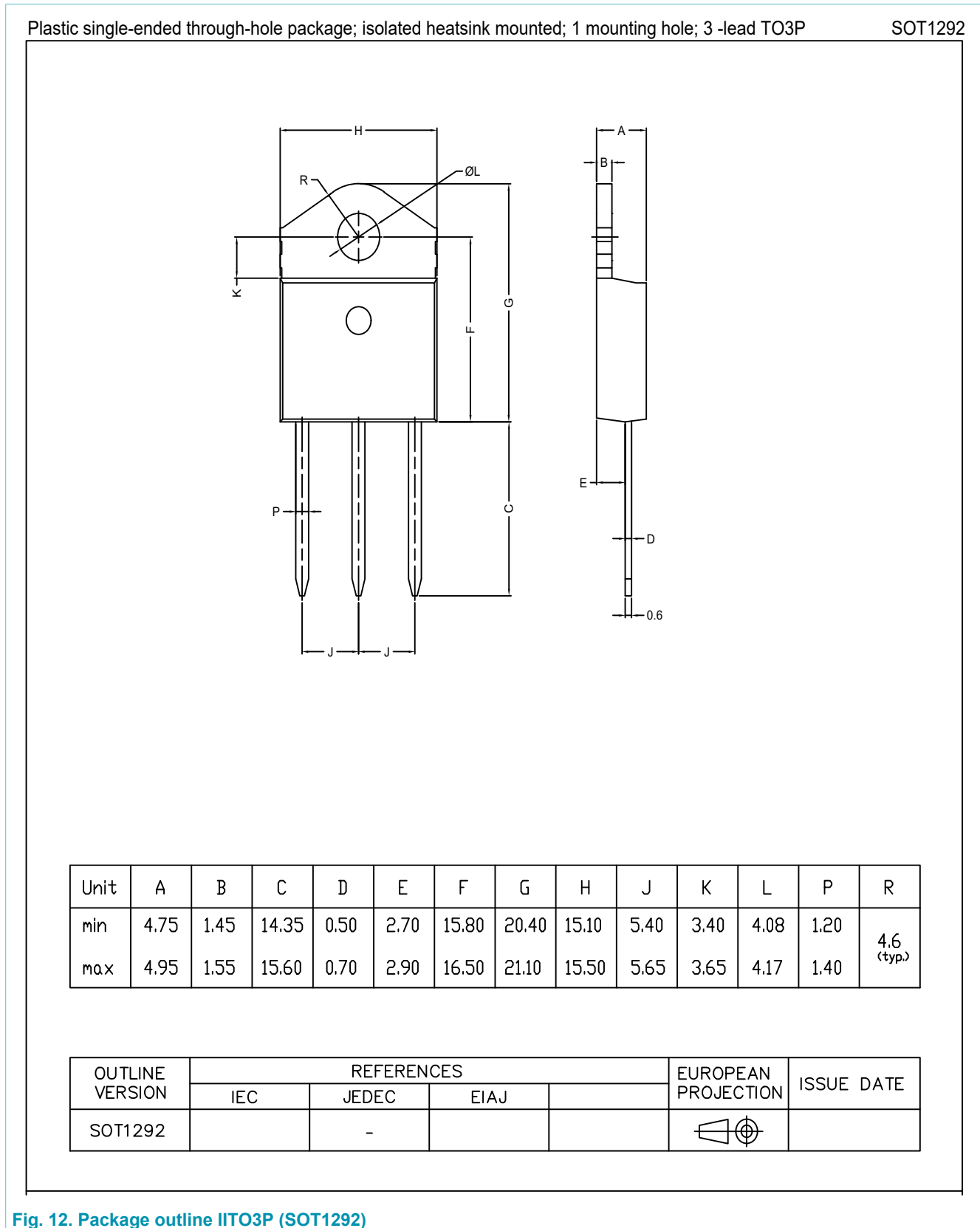


Fig. 12. Package outline ITO3P (SOT1292)

## 13. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 31 October 2016

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